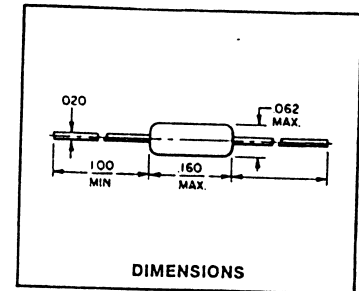


1N5605 1N5606 1N5607 1N5608 1N5609[®]
 GENERAL PURPOSE DIODES

GENERAL PURPOSE SILICON DIODES

This device is a Silicon Double Plug Diode for general purpose use in computer, industrial and military applications.



ABSOLUTE MAXIMUM RATINGS

Storage temperature range, T_{stg} -65°C to +200°C
 Lead or terminal temperature at a distance not less than
 1/16" from the seated surface (or case) for 15 seconds +275°C

	1N5605	1N5606	1N5607	1N5608/9
Reverse voltage, 25°C, free air	70 V	150 V	200 V	120 V
Maximum steady state power dissipation at 25°C, free air	250mw	200mw	200mw	250mw
Derating factor				2mw/°C

ELECTRICAL CHARACTERISTICS

	1N5605		1N5606*		1N5607*	
	MIN	MAX	MIN	MAX	MIN	MAX
Forward Voltage, V_f @ $I_f = 20$ ma		1.0 V		1.0 V		1.0 V
Breakdown Voltage, B_{vr} $I_r = 100$ ua	70 V		150 V		200 V	
Reverse Current, I_r @ $V_r = 60$ V		25 na		25 na		25 na
Reverse Current, I_r @ $V_r = 60$ V @ 150°C		5 ua		5 ua		5 ua

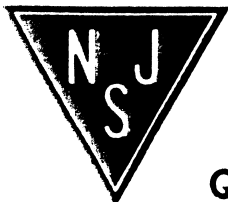
* $I_f = 7$ ma, $V_r = 125$ V

* $I_f = 3$ ma, $V_r = 175$ V

1N5605 1N5606 1N5607 1N5608

ELECTRICAL CHARACTERISTICS — 1N5608

	MIN	MAX
Forward Voltage, V_f @ $I_f = 100$ ma		1.0 V
Breakdown Voltage, B_{vr} $I_r = 100$ ua	120 V	
Reverse Current, I_r @ 50 V		50 na
Reverse Current, I_r @ 50 V @ 150°C		25 ua
*Reverse Recovery Time, T_{rr} $I_f = 5$ ma, $V_r = 40$ V $R_1 = 2$ K, $C_1 = 10$ pf Recover to 80K ohms		300 nsec



Quality Semi-Conductors